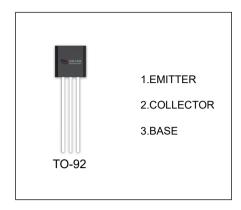


2SB1426 TRANSISTOR (PNP)

FEATURES

General Purpose Switching and Amplification



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SB1426	TO-92	Bulk	1000pcs/Bag
2SB1426-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-20	V
V _{CEO}	Collector-Emitter Voltage	-20	V
V _{EBO}	Emitter-Base Voltage	-6	V
Ic	Collector Current -Continuous	-3	А
P _D	Collector Power Dissipation	750	mW
R _{0 JA}	Thermal Resistance *rom Junction *o Ambient	166	°C /W
T_J , T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃



T_a=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.05mA,I _E =0	-20			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA,I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.05mA,I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-20V,I _E =0			-0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =-5V,I _C =0			-0.1	μΑ
DC current gain	h _{FE}	V _{CE} =-2V, I _C =-0.1A	82		390	
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =-2A,I _B =-0.1A			-0.5	V
Collector output capacitance	Cob	V _{CB} =-10V,I _E =0, f=1MHz		35		pF
Transition frequency	f _T	Vc=2V,Ic=-0.5A, f=100MHz		240		MHz

^{*}Pulse test

CLASSIFICATION OF h_{FE}

RANK	Р	Q	R
RANGE	82-180	120-270	180-390